

WHAT IS CLAIMED IS:

1. An alignment mark configuration, which is applicable on a substrate comprising a plurality of layers, the alignment mark configuration comprising:

5 an alignment mark on the substrate, wherein the alignment mark comprises a plurality of recesses and a spacing between the neighboring recesses is “d”; and

a trench, wherein a spacing between the trench and the alignment mark is in a range between about 5d to 80d.

10 2. The alignment mark configuration according to claim 1, wherein the recesses include a plurality of trenches formed by a shallow trench isolation fabrication process.

15 3. The alignment mark configuration according to claim 1, wherein the trench includes a shallow trench isolation structure.